

TECHNICAL DATA
DATA SHEET 877, REV. B**SILICON ULTRA-FAST RECOVERY EPITAXIAL
RECTIFIER DIE****Applications:**

- Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

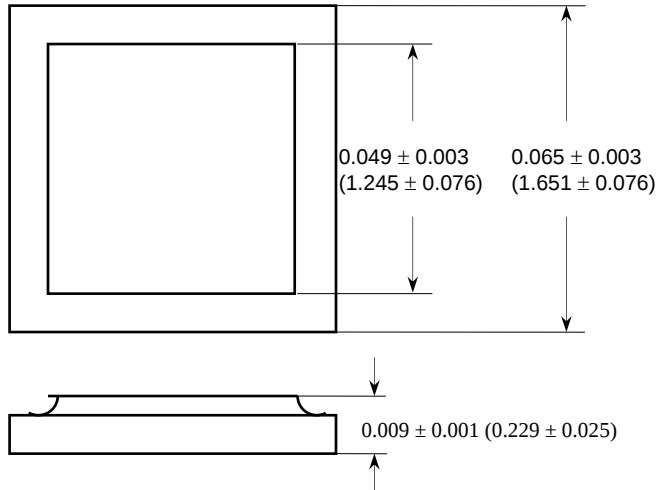
- Glass Passivated Epitaxial Diode with Mesa Structure
- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop and Low Reverse Current
- Electrically and Mechanically Stable during and after Packaging

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^\circ\text{C}$ unless otherwise specified.

Rating	Symbol	Condition	Max	Units
WORKING PEAK REVERSE VOLTAGE 1C6626 1C6627 1C6628 1C6629 1C6630 1C6631	V_{RWM}		200 400 600 800 900 1000	Volts
AVERAGE RECTIFIED FORWARD CURRENT 1C6626 thru 1C6628 1C6629 thru 1C6631	I_o	$T_A = 75^\circ\text{C}$	2.3 1.8	Amps
PEAK FORWARD SURGE CURRENT 1C6626 thru 1C6630 1C6631	I_{FSM}	$T_p = 8.3\text{ms}$	75 60	A(pk)
MAXIMUM REVERSE CURRENT 1C6626 thru 1C6630 1C6631	$I_R @ V_{RWM}$	$T_j = 25^\circ\text{C}$	2.0 4.0	μAmps
MAXIMUM REVERSE CURRENT 1C6626 thru 1C6630 1C6631	$I_R @ V_{RWM}$	$T_j = 150^\circ\text{C}$	500 600	μAmps
MAX. PEAK FORWARD VOLTAGE (PULSED) 1C6626 thru 1C6628 1C6629 to 1C6630 1C6631	V_{FM}	$I_F = 4\text{A}$ $I_F = 3\text{A}$ $I_F = 2\text{A}$	1.50 1.70 1.95	Volts
MAXIMUM REVERSE RECOVERY TIME 1C6626 thru 1C6628 1C6629 to 1C6630 1C6631	T_{rr}	$I_F = 0.5\text{A}$ $I_{RM} = 1.0\text{A}$	30 50 60	ns

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Dimensions in inches (mm):



Bottom side metalization: Ti/Ni/Ag - 30 kÅ minimum.

Top side metalization: Al - 25 kÅ minimum

Bottom side is cathode, top side is anode.

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